

# Hae Jin Kim

## List of Publications by Year in descending order

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22  
papers

622  
citations

516710

16  
h-index

794594

19  
g-index

22  
all docs

22  
docs citations

22  
times ranked

1135  
citing authors

#	ARTICLE	IF	CITATIONS
1	Nociceptive Memristor. <i>Advanced Materials</i> , 2018, 30, 1704320.	21.0	116
2	Nucleation-Limited Ferroelectric Orthorhombic Phase Formation in Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Thin Films. <i>Advanced Electronic Materials</i> , 2019, 5, 1800436.	5.1	55
3	Thickness effect of ultra-thin Ta <sub>2</sub> O <sub>5</sub> resistance switching layer in 28 nm-diameter memory cell. <i>Scientific Reports</i> , 2015, 5, 15965.	3.3	51
4	Fabrication of a Cone-Shaped Cation Source Inserted Conductive Bridge Random Access Memory and Its Improved Switching Reliability. <i>Advanced Functional Materials</i> , 2019, 29, 1806278.	14.9	51
5	Double-Layer-Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 <sup>9</sup> . <i>Advanced Electronic Materials</i> , 2017, 3, 1700152.	5.1	42
6	Hierarchical assembly of TiO <sub>2</sub> -SrTiO <sub>3</sub> heterostructures on conductive SnO <sub>2</sub> backbone nanobelts for enhanced photoelectrochemical and photocatalytic performance. <i>Journal of Hazardous Materials</i> , 2014, 275, 10-18.	12.4	37
7	A Stateful Logic Family Based on a New Logic Primitive Circuit Composed of Two Antiparallel Bipolar Memristors. <i>Advanced Intelligent Systems</i> , 2020, 2, 1900082.	6.1	36
8	Defect-Engineered Electroforming-Free Analog HfO <sub>x</sub> Memristor and Its Application to the Neural Network. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 47063-47072.	8.0	33
9	Surface-area-tuned, quantum-dot-sensitized heterostructured nanoarchitectures for highly efficient photoelectrodes. <i>Nano Research</i> , 2014, 7, 144-153.	10.4	25
10	Filament Shape Dependent Reset Behavior Governed by the Interplay between the Electric Field and Thermal Effects in the Pt/TiO <sub>2</sub> /Cu Electrochemical Metallization Device. <i>Advanced Electronic Materials</i> , 2017, 3, 1600404.	5.1	24
11	Investigation of the retention performance of an ultra-thin HfO <sub>2</sub> resistance switching layer in an integrated memory device. <i>Journal of Applied Physics</i> , 2018, 124, .	2.5	24
12	Single-Cell Stateful Logic Using a Dual-Bit Memristor. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1800629.	2.4	23
13	A study of the transition between the non-polar and bipolar resistance switching mechanisms in the TiN/TiO <sub>2</sub> /Al memory. <i>Nanoscale</i> , 2016, 8, 16455-16466.	5.6	22
14	Roles of conducting filament and non-filament regions in the Ta <sub>2</sub> O <sub>5</sub> and HfO <sub>2</sub> resistive switching memory for switching reliability. <i>Nanoscale</i> , 2017, 9, 6010-6019.	5.6	22
15	Balancing the Source and Sink of Oxygen Vacancies for the Resistive Switching Memory. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 21445-21450.	8.0	21
16	Thickness-dependent electroforming behavior of ultra-thin Ta <sub>2</sub> O <sub>5</sub> resistance switching layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015, 9, 362-365.	2.4	19
17	Novel Selector-Induced Current-Limiting Effect through Asymmetry Control for High-Density One-Selector-One-Resistor Crossbar Arrays. <i>Advanced Electronic Materials</i> , 2019, 5, 1800806.	5.1	10
18	Multi-Level Control of Conductive Filament Evolution and Enhanced Resistance Controllability of the Cone Structure Embedded Conductive Bridge Random Access Memory. <i>Advanced Electronic Materials</i> , 0, , 2100209.	5.1	6

#	ARTICLE	IF	CITATIONS
19	Bipolar resistive switching property of Si <sub>3</sub> N <sub>4</sub> thin films depending on N deficiency. Journal of Materials Chemistry C, 2020, 8, 1755-1761.	5.5	4
20	Next-Generation Memory: Double-Layer Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 <sup>9</sup> (Adv. Electron. Mater. 7/2017). Advanced Electronic Materials, 2017, 3, .	5.1	1
21	Stateful logic circuit and material using memristors. , 2017, , .		0
22	Cu cone inserted CBRAM device fabrication and its improved switching reliability induced by field concentration effect. , 2018, , .		0